



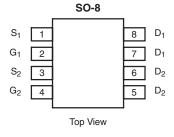
N- and P-Channel 2.5-V (G-S) MOSFET

PRODUCT SUMMARY				
	V _{DS} (V)	$R_{DS(on)}(\Omega)$	I _D (A)	
N-Channel	20	0.025 at V _{GS} = 4.5 V	7.1	
		0.035 at V _{GS} = 2.5 V	6.0	
P-Channel	- 20	0.033 at V _{GS} = - 4.5 V	- 6.2	
		0.050 at V _{GS} = - 2.5 V	- 5.0	

FEATURES

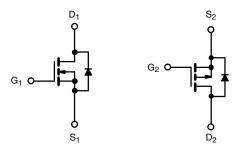
- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET[®] Power MOSFET: 2.5 Rated
- Compliant to RoHS directive 2002/95/EC





Ordering Information: Si4562DY-T1-E3 (Lead (Pb)-free)

Si4562DY-T1-GE3 (Lead (Pb)-free and Halogen-free)



N-Channel MOSFET

P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS T _A = 25 °C, unless otherwise noted						
Parameter		Symbol	N-Channel	P-Channel	Unit	
Drain-Source Voltage		V_{DS}	20	- 20	V	
Gate-Source Voltage		V_{GS}	± 12		7 ' !	
Continuous Drain Current (T _{.I} = 150 °C) ^a	T _A = 25 °C	I_	7.1	- 6.2		
Continuous Diairi Current (1 j = 150°C)	T _A = 70 °C	ID	5.7	- 4.9	Α	
Pulsed Drain Current		I _{DM}	40	- 40	7	
Continuous Source Current (Diode Conduction) ^a		I _S	1.7	- 1.7		
Maximum Power Dissipation ^a	T _A = 25 °C	P _D	2.0		w	
Maximum Fower Dissipation	T _A = 70 °C	' D	1.3			
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55	°C		

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	N- or P-Channel	Unit		
Maximum Junction-to-Ambient ^a	R _{thJA}	62.5	°C/W		

Notes:

a. Surface Mounted on FR4 board, $t \le 10 \text{ s.}$

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Parameter	Symbol	Test Conditions		Min.	Тур.	Max.	Unit
Static			<u> </u>				
Gate Threshold Voltage	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	N-Ch	0.6		1.6	V
	V _{GS(th)}	V _{DS} = V _{GS} , I _D = - 250 μA	P-Ch	- 0.6		- 1.6	
Gate-Body Leakage		$V_{DS} = 0 \text{ V}, V_{GS} = \pm 12 \text{ V}$	N-Ch			± 100	nΛ
	I _{GSS}		P-Ch			± 100	nA
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = 20 \text{ V}, V_{GS} = 0 \text{ V}$	N-Ch			1	
		$V_{DS} = -20 \text{ V}, V_{GS} = 0 \text{ V}$	P-Ch			- 1	μΑ
Zero date Voltage Brain Garrent	.033	$V_{DS} = 20 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55 ^{\circ}\text{C}$	N-Ch			5	μΑ
		$V_{DS} = -20 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55 ^{\circ}\text{C}$	P-Ch			- 5	
On-State Drain Current ^b		$V_{DS} \ge 5 \text{ V}, V_{GS} = 4.5 \text{ V}$	N-Ch	20			А
	I _{D(on)}	$V_{DS} \le -5 \text{ V}, V_{GS} = -4.5 \text{ V}$	P-Ch	- 20			
		V _{GS} = 4.5 V, I _D = 7.1 A	N-Ch		0.019	0.025	Ω
		V _{GS} = - 4.5 V, I _D = - 6.2 A	P-Ch		0.027	0.033	
Drain-Source On-State Resistance ^b	R _{DS(on)}	$V_{GS} = 2.5 \text{ V}, I_D = 6.0 \text{ A}$	N-Ch		0.025	0.035	
		V _{GS} = - 2.5 V, I _D = - 5.0 A	P-Ch		0.040	0.050	
Forward Transconductance ^b	g _{fs}	$V_{DS} = 10 \text{ V}, I_{D} = 7.1 \text{ A}$	N-Ch		27		S
		V _{DS} = - 10 V, I _D = - 6.2 A	P-Ch		20		
b	V _{SD}	I _S = 1.7 A, V _{GS} = 0 V	N-Ch			1.2	V
Diode Forward Voltage ^b		I _S = - 1.7 A, V _{GS} = 0 V	P-Ch			- 1.2	V
Dynamic ^b							
Total Gate Charge	Qg	N-Channel V _{DS} = 10 V, V _{GS} = 4.5 V, I _D = 7.1 A	N-Ch		25	50	
Total date onlinge	G g		P-Ch		22	35	
Gate-Source Charge	Q_{gs}	VDS = 10 V, VGS = 4.5 V, ID = 7.1 /	N-Ch		6.5		nC
	90	P-Channel V _{DS} = - 10 V, V _{GS} = - 4.5 V, I _D = - 6.2 A	P-Ch		7		
Gate-Drain Charge	Q_{gd}		N-Ch P-Ch		4 3.5		
			N-Ch		40	60	
Turn-On Delay Time	t _{d(on)}	N-Channel	P-Ch		27	50	
Rise Time	t _r	$V_{DD} = 10 \text{ V}, R_L = 10 \Omega$	N-Ch		40	60	
		$I_D \cong 1 \text{ A}, V_{GEN} = 4.5 \text{ V}, R_g = 6 \Omega$	P-Ch		32	50	
Turn-Off Delay Time	t _{d(off)}	P-Channel	N-Ch		90	150	ns
Tarri Sir Dolay Time	-u(OII)	V_{DD} = - 10 V, R_L = 10 Ω	P-Ch		95	150	115
Fall Time	t _f	$I_D \cong$ - 1 A, V_{GEN} = - 4.5 V, R_g = 6 Ω	N-Ch		40	60	
-		1 1 7 A All/-th 100 A/	P-Ch		45	70	
Sorce-Drain Reverse Recovery Tme	t _{rr}	$I_F = 1.7 \text{ A}, \text{ dI/dt} = 100 \text{ A/}\mu\text{s}$	N-Ch		40	80	
		$I_F = -1.7 \text{ A}, dI/dt = 100 \text{ A/}\mu\text{s}$	P-Ch		40	80	

Notes:

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

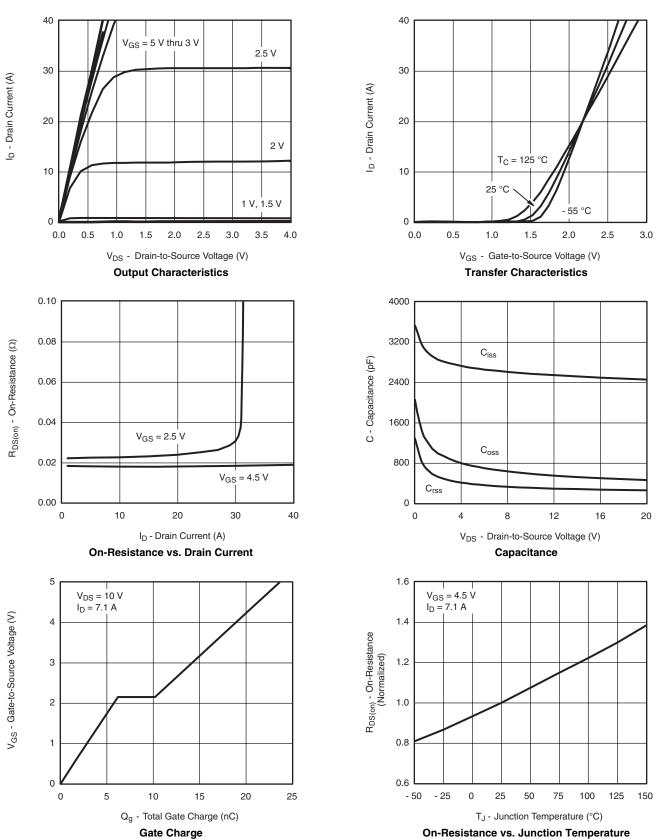
a. For design aid only; not subject to production testing. b. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %.







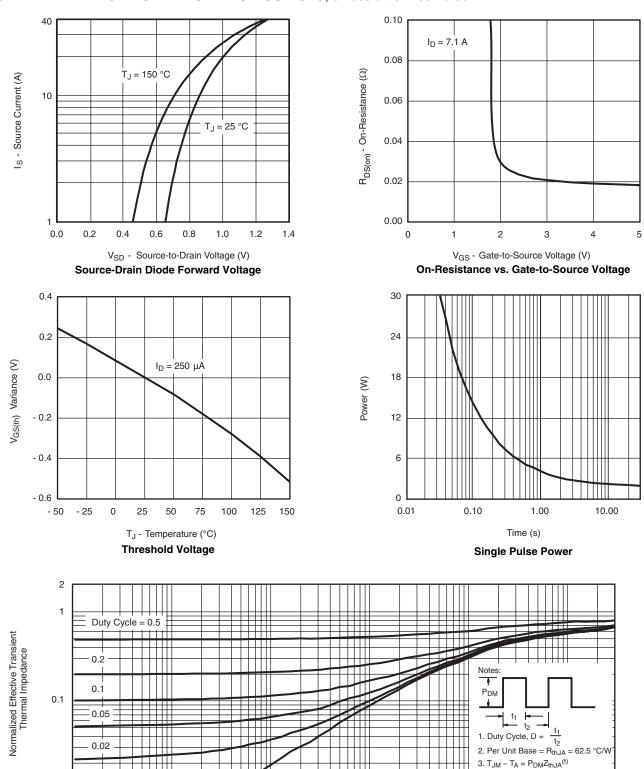
N-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



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N-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Square Wave Pulse Duration (s)

Normalized Thermal Transient Impedance, Junction-to-Ambient

10⁻¹

10⁻²

Single Pulse

10-3

0.01

10-4

30

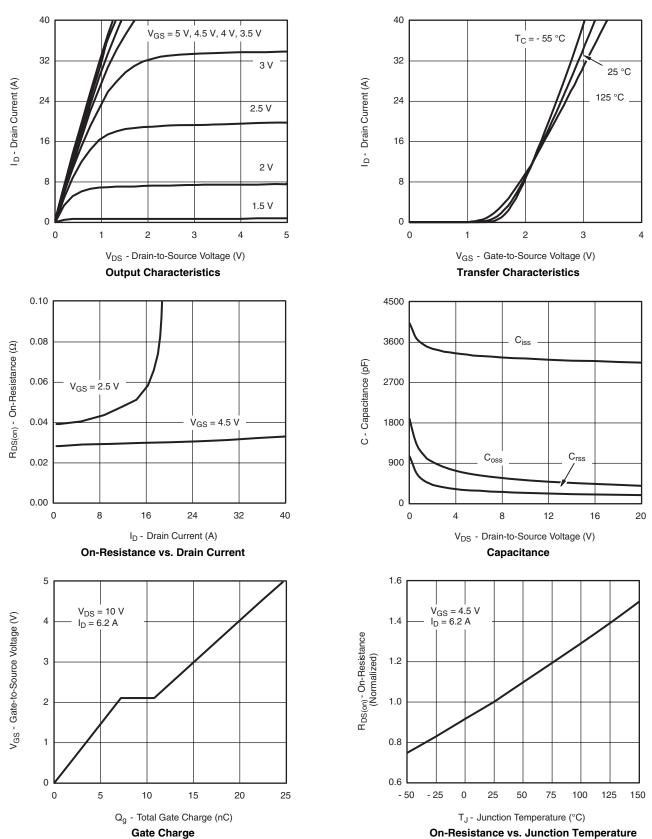
10

4. Surface Mounted





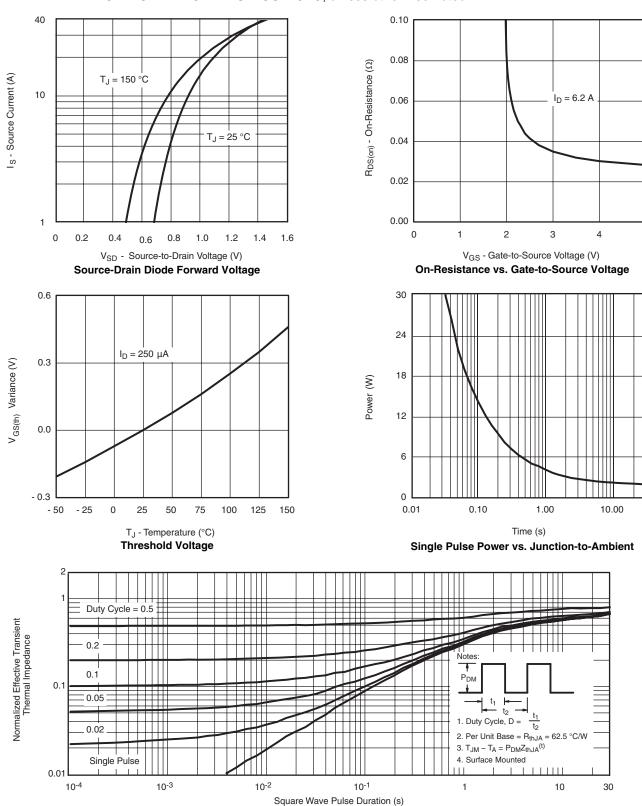
P-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



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P-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Ambient

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